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U.S. PATENT DOCUMENTS

Examiner		Document				MAR U 7 1999
Initial		Number	Date	Name	Class	Subclass
Idle	AA	5,652,724	7/97	Manning	√ 365	189.05 Group 2700
A	AB	5,457,659	10/95	Schaefer	365	222
	AC	5,452,261	9/95	Chung et al.	₹ 265	233
	AD	5,280,594	1/94	Young et al.	¥395711	125/57
	AE	5,058,066	10/91	Yu	√ 365	189.05
	AF	4,870,622	9/89	Aria et al.	√ 365	230.02
	AG	5,668,773	09/97	Zagar et al.	₹ 365	233
	AH	5,325,502	06/94	McLaury	295711	425 169
	AI	5,373,227	12/94	Keeth	323	313
V	AJ	5,410,670	04/95	Hansen et al.	393 711	428/69
ish	AK	5,349,566	09/94	Merritt et al.	365	233.5

FOREIGN PATENT DOCUMENTS

Examiner		Document					Trans	lation
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	AL	- "						
	AM							
	AN							
	AO							
	AP							
	AQ							

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OTHER ART (including author, title, date, pertinent pages, etc.)

Micron Technology, Inc., "1995 DRAM Data Book" pp. 4-1 thru 4-42, 12/95

"Rossini, Pentium, PCI-ISA, Chip Set", Symphony Laboratories, entire book.

AT PCT Patent Application No. PCT/US95/16984, filed 12/22/1995, entitled: Burst Edo Memory Device.

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FORM: PTO-1449	U.S. DEPARTMENT OF COMMERCE	Atty Docket No:	Serial No:
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			U.	S. PATENT DOCUMENTS	RECEIVED	
Examiner		Document				-CLIVED
Initial		Number	Date	Name	Class	Sub Mass (1 y 1999
SIL	AA	5,682,354	10/97	Manning	365	
ril.	AB	5,640,364	06/97	Merritt et al.	365	2325 236 FOUO 2700
Ill	AC	5,729,504	12/95	Cowles	. 365	236 1000 2700
The	AD	5,661,695	08/97	Zagar et al.	365	233.5
ilh	AE	5,305,284	04/94	Iwase	365	238.5
1dh	AF	5,325,330	06/94	Morgan	365	189.05
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FOREIGN PATENT DOCUMENTS

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	AP							
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OTHER ART (including author, title, date, pertinent pages, etc.)

PCT Patent Application No. PCT/US95/16656, filed 12/21/1995, entitled: Burst Edo Memory Device Address Counter.

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U.S. PATENT DOCUMENTS

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Examiner		Document				UAIT 1 1777
Initial		Number	Date	Name	Class	Subclass Oup 2700
idle	AA	5,357,469	10/18/94	Sommer et al.	365	193 4.040 2700
A	AB	5,268,865	12/7/93	Takasugi	365	189.5
	AC	4,618,947	10/21/86	Tran et al.	√ 365	2 30 236
	AD	5,267,200	11/30/93	Tobita	365	189.5189.05
	AE	4,344,156	8/10/82	Eaton et al.	₹ 365	203/89.05
	AF	4,707,811	11/17/87	Takemae et al.	₩ 365	239
	AG	4,649,522	3/10/87	Kirsch	¥ 365	189, 05
	AH	4,603,403	7/29/86	Toda	365	189.05
	ΑI	4,567,579	1/28/86	Patel et al.	365	189.05
L L	AJ	4,484,308	11/20/84	Lewandowski et al.	¥ 365711	900 109
Idh	AK	4,875,192	10/17/89	Matsumoto	365	193

FOREIGN PATENT DOCUMENTS

Examiner		Document					Trans	lation
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	AL							
	AM			2 10 101				
-	AN							
	AO							
	AP							
	AQ							

Initial

OTHER ART (including author, title, date, pertinent pages, etc.)

Samsung Electronics, "Samsung Synchronous DRAM", March 1993, pgs. 1-16

Oki Electric Ind. Co., Ltd., "Burst DRAM Function & Pinout", 2nd presentation, Item #619, September, 1994

AS

Toshiba, "Pipelined Burst DRAM", December 1994, JEDEC JC-42.3 Hawaii

Examiner:	Н.	Kim	Date Considered: 3/12/99	

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FORM: PTOCKOLDARY	U.S. DEPARTMENT OF COMMERCE	Atty Docket No:	Serial No:	_
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U.S. PATENT DOCUMENTS

Examiner		Document				
Initial		Number	Date	Name	Class	Subclass
Ne	AA	4,685,089	8/4/87	Patel et al.	365	235189.05
_	AB	4,562,555	12/31/85	Ouchi et al.	y 365	233189,03
	AC	4,575,825	3/11/86	Ozaki et al.	4 365	189/93
	AD	4,788,667	11/29/88	Nakano	365	193
	AE	5,392,239	2/21/95	Margulis et al.	365	189. 01
	AF	5,379,261	1/3/95	Jones, Jr.	√ 365	230.01
1	AG	5,126,975	6/30/92	Handy et al.	365	230.01
	AH	5,331,593	7/94	Merritt	365	189.11
U	ΑI	5,311,471	5/90	Matsumoto	365	189.05
Ill	AJ	5,526,320	6/11/96	Zagar et al.	√ 365	233.5

FOREIGN PATENT DOCUMENTS

Examiner		Document					Trans	lation
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Initial OTHER ART (including author, title, date, pertinent pages, etc.)

IIIItiai		O I I Die Met (moraum g audior, thio, date, pertinent pages, etc.)
Ille	AR	Toshiba America Electronic Components, Inc., "Application Specific DRAM, 1994", Pgs. C-178, C-260, C218
ish	AS	Micron Semiconductor, Inc., "Synchronous DRAM 2 MEG x 8 SDRAM", Pgs. 2-3 through 2-6, Rev. 4/94
(th	AT	Toshiba America Electronic Components, Inc., "4M DRAM 1991", Pgs. A-137 - A-159

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Examiner		Document		U.S. PATENT DOCUME	NIS		
Initial		Number	Date	Name	Class	Subclass	
124	AA	5,268,865	12/93	Takasugi	365	189.05	· · ·
<u> </u>	AB	5,319,759	6/94	Chan	365711	230.08217	
	AC	5,327,390	7/94	Takasugi	365	230,000	230,06
	AD	5,426,606	6/95	Takai	365	230.06	189.05
W.	AE	5,369,622	11/94	McLaury	365	233	1011
1sh	AF	5,568,445	10/96	Park et al.	365	233	
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U.S. DEPARTMENT OF COMMERCE

PATENT AND TRADEMARK OFFICE

Initial		OTHER ART (including author, title, date, pertinent pages, etc.)
(Sh	AR	Micron Semiconductor, Inc., "1994 DRAM Data Book", pgs. 2-1 to 2-6
ıll	AS	Mosel-Vitelic V53C8257H DRAM Specification Sheet, 20 pgs.
(Jk	AT	Toshiba Corp., "Integrated Circuit Technical Data-262,144 Words x 8 Bits Multiport DRAM", TC52826TS/Z/FT/TR, TEN. Rev. 2.1

Examiner:	H. Cim	Date Considered: 3/12/99
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		Mid	ron Technology	y, Inc., "Burst EDO DRAM	I Information", pgs. 1-126	, Rev. 9/95		
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	 	NE	C "Command T	ruth Table" March 15, 199	2			
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	 	San	nsung Electronic	cs "KM48SV2000 Prelimin	nary CMOS SDRAM" Rev	1.1(Mar, 1993), pgs. 7-8	
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1ste 1ste	AS AT		DRAM 1 Meg X 4 icron Technology,	DRAM 5BEDO Page M I)	Iode",", <u>1995 DRAM</u>	1 Data E	Book, pp.1-1	thru 1-30,,
WE		(M		I)		I Data E	Book, pp.1-1	thru 1-30,,
						f Data E	Book, pp.1-1	thru 1-30,,

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U.S. PATENT DOCUMENTS

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FOREIGN PATENT DOCUMENTS

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Initial		Number	Date	Country	Class	Subclass	Yes	No
	AL							
	AM							
•	AN							
	AO							
	AP							
	AQ							

"Hyper Page Mode DRAM", 8029 Electronic Engineering, 66, No. 813, Woolwich, London, GB, pp. 47-48, (September 1994)

Dave Bursky, "Novel I/O Options and Innovative Architectures Let DRAMs Achieve SRAM

Performance; Fast DRAMS can be swapped for SRAM Caches", Electronic Design, Vol. 41, No. 15,

Cleveland, Ohio, pp. 55-67, (July 22, 1993)

OTHER ART (including author, title, date, pertinent pages, etc.)

Cleveland, Ohio, pp. 55-67, (July 22, 1993)

Shiva P. Gowni, et al., "A 9NS, 32K X 9, BICMOS TTL Synchronous Cache RAM With Burst Mode
ACCESS", IEEE, Cutsom Integrated Circuits Conference, pp. 781-786, (March 3, 1992)

Examiner: H. Cim	Date Considered: 3/12/99	

EXAMINER:

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Sheet: 7 of: 8

FORM: PTO	1: PTO-1449 : 7-80)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		Atty Docket No: 95-0653.03		Serial No: 08/984,563			
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n		Micron Semiconductor, Inc., "Synchronous DRAM 4 Meg x 4 SDRAM", Pgs. 2-1 to 2-2								
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11/2	Micron Technology, Inc., "1996 DRAM Data Book", Pgs. 1-1 to 1-52, and 4-1 to 4-42									
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		Micron Technology, Inc., "1995 DRAM Data Book", Pgs. 3-1 to 3-37								
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			ccess" IFFF	Justom Integrated Circuite	onference_pp	781 786 (M	arch 2_1002\	- ·	
• • •	AS-	As Access", IEEE, Custom Integrated Circuits Conference, pp. 781–786, (March 3, 1992). /S3 Incorporated, "S3 Burst Mode-DRAM", 6/93, 2 pages							
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